TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2401

Chopper Regulator, DC-DC Converter and Motor Drive Applications

 $\begin{array}{ll} \bullet & \text{Low drain-source ON resistance} & : R_{DS} \ (ON) = 0.13 \ \Omega \ (typ.) \\ \bullet & \text{High forward transfer admittance} & : |Y_{fs}| = 17 \ S \ (typ.) \\ \bullet & \text{Low leakage current} & : I_{DSS} = 100 \ \mu\text{A} \ (max) \ (V_{DS} = 200 \ V) \\ \end{array}$

• Enhancement-mode : $V_{th} = 1.5 \sim 3.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	200	V
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	200	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I _D	15	Α
	Pulse (Note 1)	I _{DP}	45	Α
Drain power dissipation (Tc = 25°C)		P_{D}	75	W
Single pulse avalanche energy (Note 2)		E _{AS}	166	mJ
Avalanche current		I _{AR}	15	Α
Repetitive avalanche energy (Note 3)		E _{AR}	7.5	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature range		T _{stg}	-55~150	°C

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	1.67	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W

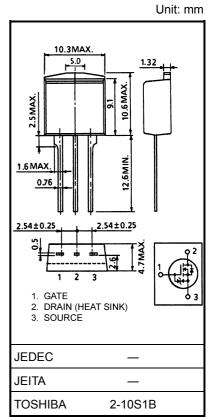
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 1.2 mH, R_G = 25 Ω , I_{AR} = 15 A

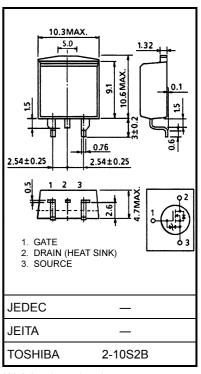
Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.



Weight: 1.5 g (typ.)



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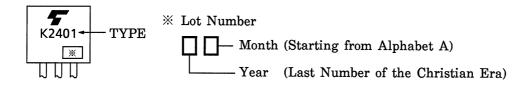
Electrical Characteristics (Ta = 25°C)

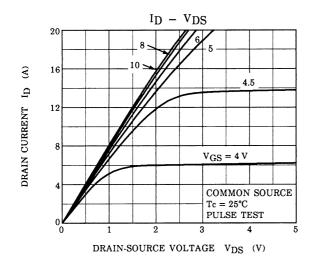
Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V		_	100	μΑ
Drain-source bi	reakdown voltage	V _{(BR) DSS}	I _D = 10 mA, V _{GS} = 0 V	200	_	_	V
Gate threshold v	/oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	1.5	_	3.5	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 10 A		0.13	0.18	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	10	17	_	S
Input capacitano	е	C _{iss}			2000	_	
Reverse transfe	r capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		200	_	рF
Output capacita	Output capacitance C _{oss}]		600	_	
T Switching time F	Rise time	t _r	$V_{GS} \stackrel{10 \text{ V}}{_{0 \text{ V}}} \stackrel{I_{D} = 10 \text{ A}}{\underset{R_{L}}{\downarrow}} V_{out}$ $V_{DD} = 100 \text{ V}$	_	35	_	- ns
	Turn-on time	t _{on}		_	50	_	
	Fall time	t _f		_	10	_	
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{\mathbf{W}} = 10 \ \mu \mathrm{s}$	_	66	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	40	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$		25		nC
Gate-drain ("miller") charge		Q _{gd}			15	_	

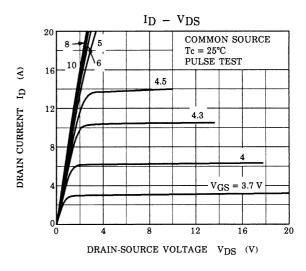
Source-Drain Ratings and Characteristics (Ta = 25°C)

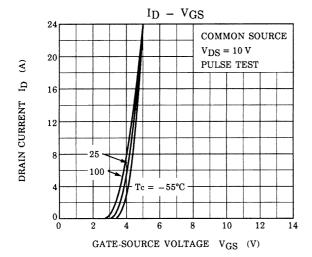
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	15	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	45	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 15 A, V _{GS} = 0 V	_	_	-2.0	V
Reverse recovery time	t _{rr}	I _{DR} = 15 A, V _{GS} = 0 V	1	180	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} / dt = 100 A / μs	_	1.13	_	μC

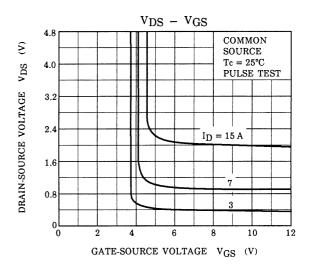
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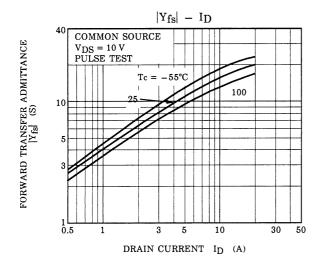


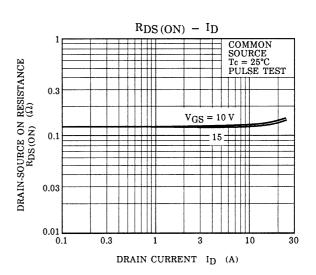




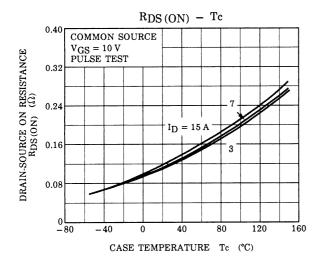


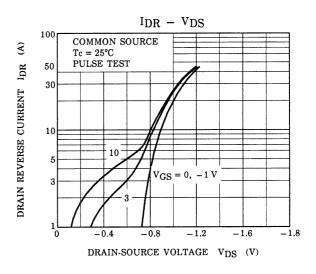


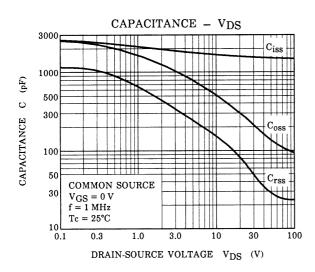


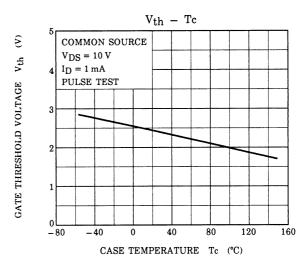


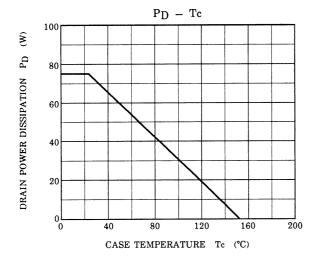
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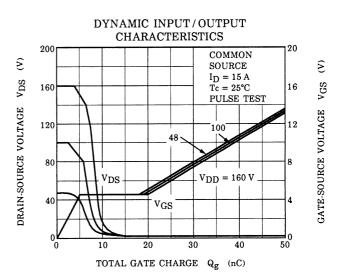


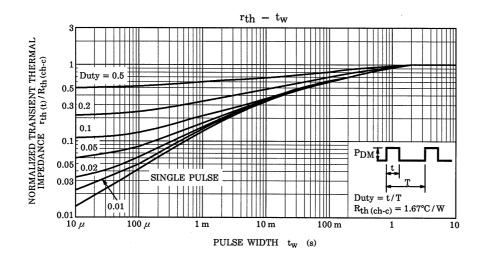


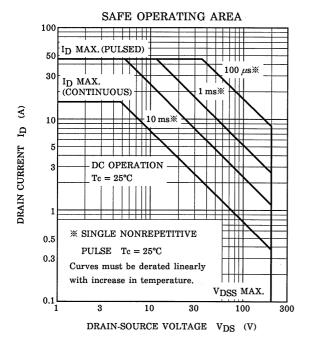


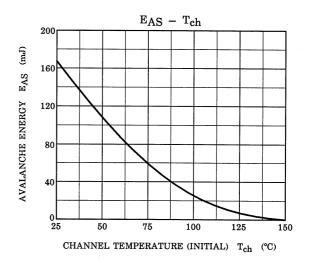


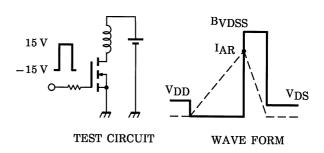












$$\begin{aligned} &R_G = 25 \ \Omega \\ &V_{DD} = 50 \ V, \ L = 1.2 \ mH \end{aligned} \qquad EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - VDD} \right)$$

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